

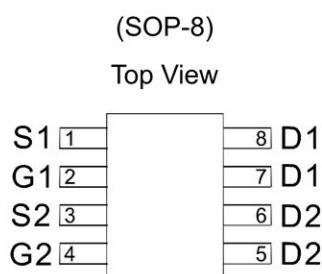
GENERAL FEATURES

- $V_{DS}=60V, I_D=6A$
- $R_{DS(ON)} < 35m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 45m\Omega @ V_{GS}=4.5V$

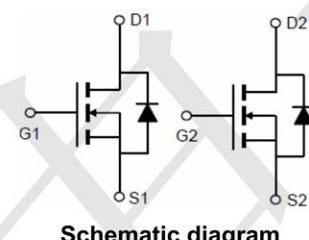
Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

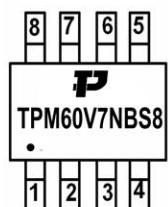
Package and Pin Configuration



Circuit diagram



Marking:



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	6	A
Drain Current-Continuous($T_c=100^\circ C$)	$I_D (100^\circ C)$	3.5	A
Pulsed Drain Current	I_{DM}	24	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	62.5	°C/W
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.2	1.6	2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=5\text{A}$	-	26	35	$\text{m}\Omega$
	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=5\text{A}$	-	32	45	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=5\text{A}$	11	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	979	-	PF
Output Capacitance	C_{oss}		-	120	-	PF
Reverse Transfer Capacitance	C_{rss}		-	100	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=30\text{V}, R_{\text{L}}=6.7\Omega, V_{\text{GS}}=10\text{V}, R_{\text{G}}=3\Omega$	-	5.2	-	nS
Turn-on Rise Time	t_{r}		-	3	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	17	-	nS
Turn-Off Fall Time	t_{f}		-	2.5	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=30\text{V}, I_{\text{D}}=5\text{A}, V_{\text{GS}}=10\text{V}$	-	22	-	nC
Gate-Source Charge	Q_{gs}		-	3.3	-	nC
Gate-Drain Charge	Q_{gd}		-	5.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=5\text{A}$	-		1.2	V
Diode Forward Current (Note 2)	I_{S}		-	-	5	A
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Typical Electrical and Thermal Characteristics

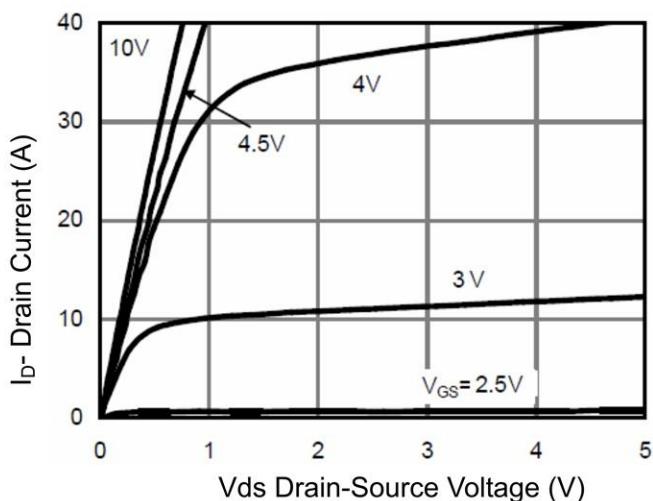


Figure 1 Output Characteristics

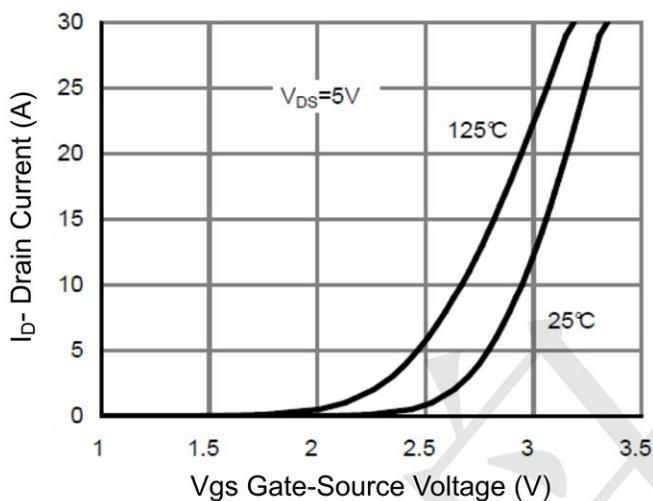


Figure 2 Transfer Characteristics

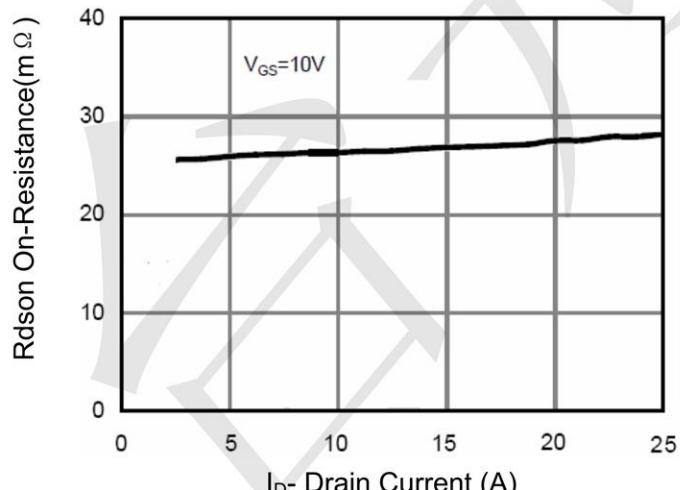


Figure 3 Rdson- Drain Current

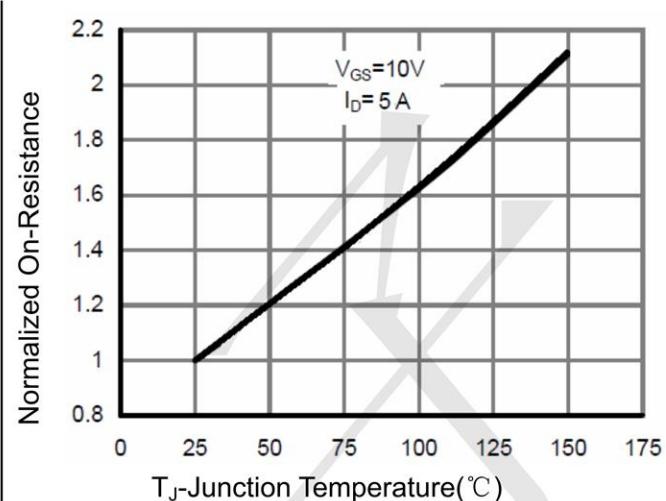


Figure 4 Rdson-Junction Temperature

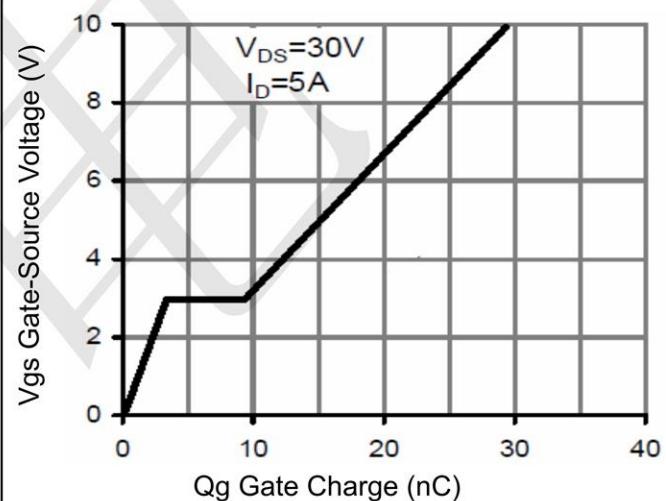


Figure 5 Gate Charge

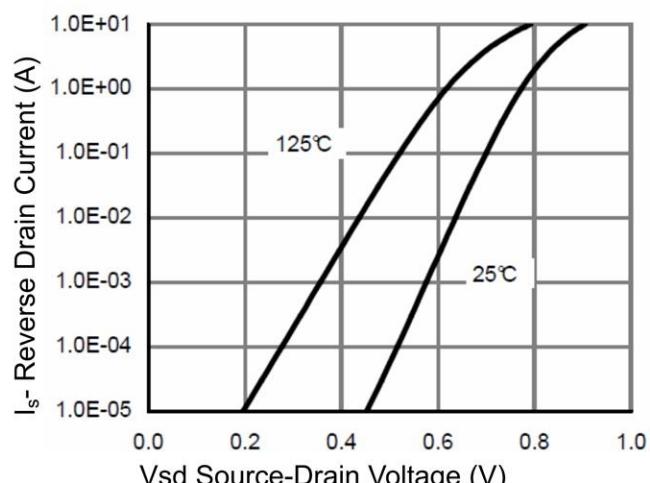
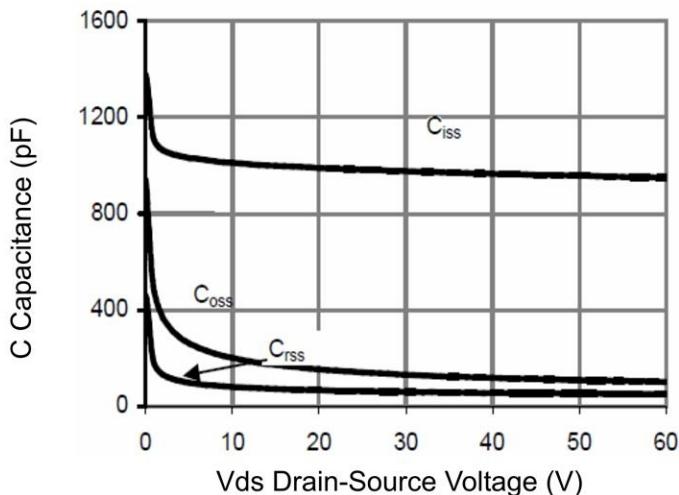
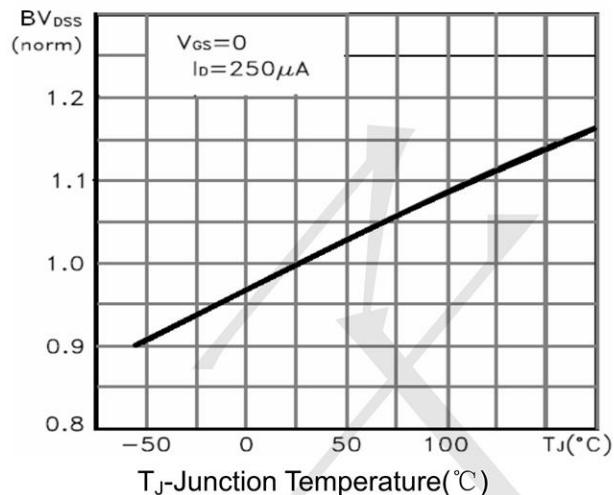
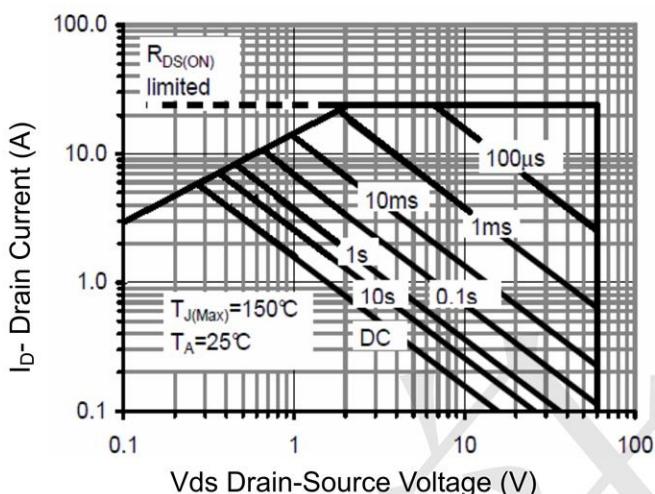
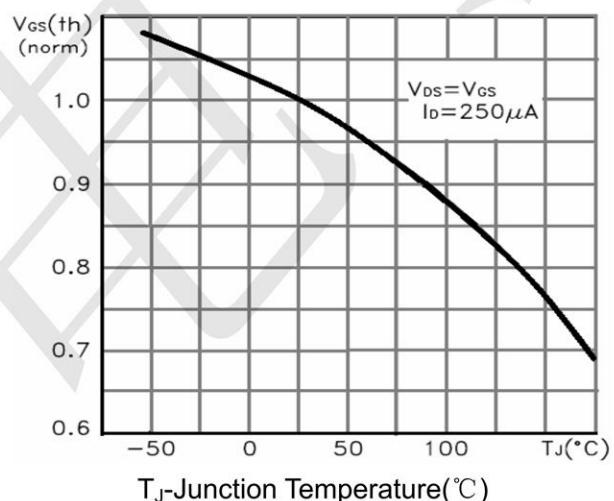
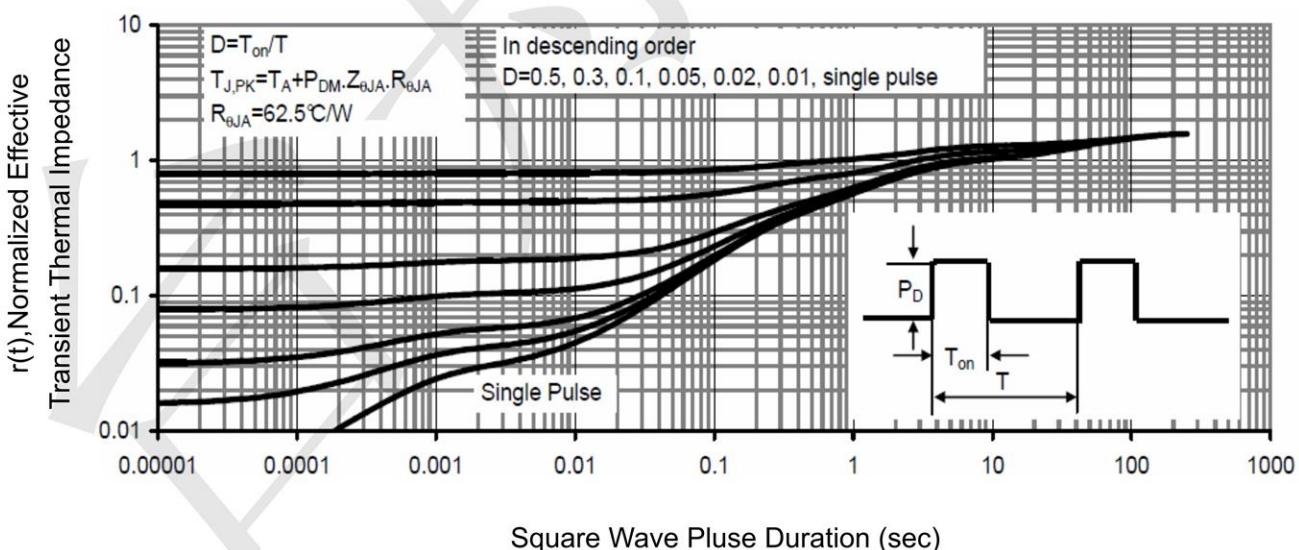
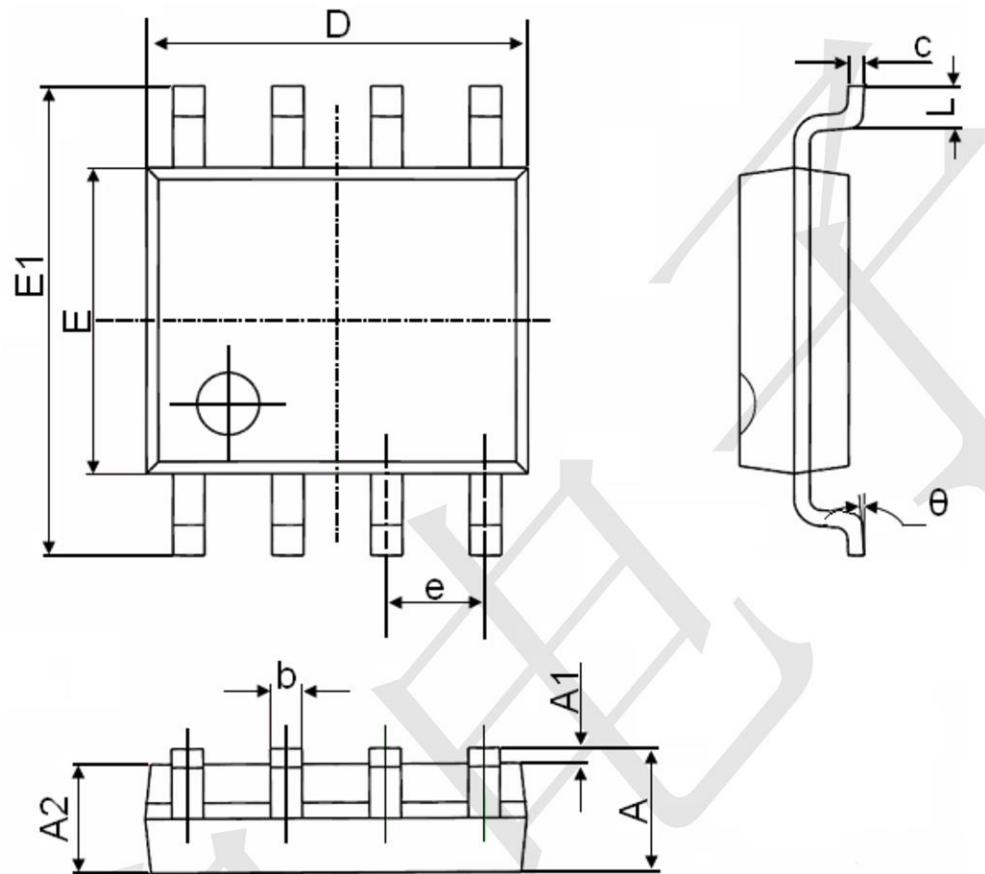


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature

Figure 8 Safe Operation Area

Figure 10 $V_{GS(th)}$ vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°